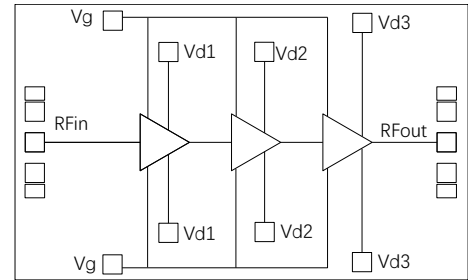


GaN MMIC Power Amplifier Chip, 6.0-18.0 GHz

Performance characteristics

- Frequency range: 6~18GHz
- Psat: 41.8dBm (pulse) /40dBm (continuous wave)
- Power gain: 18.5dB (pulse) /14dB (continuous wave)
- Power supply: 28V/-2.3V (pulse) /26V/-2.3V (continuous wave)
- 50ohm input/output
- Chip size: 4.00mm×3.00mm×0.1mm

Block Diagram



Product Introduction

GPA6-18-41 is a power amplifier chip manufactured using GaN HEMT technology. The working frequency band covers 6.0-18.0GHz and can operate under pulse (+28V power supply) and continuous wave (+26V power supply) conditions. Under a pulse supply voltage of 28V, it can provide a power gain of 18.5dB and a saturated output power greater than 41.8dBm. Under a continuous wave supply voltage of 26V, it can provide a power gain of 14dB and a saturated output power greater than 40dBm. The chip is grounded through the back through-hole. Mainly used in communication systems, high-power transceiver components, and other fields.

DC electrical parameters (T_A=+25°C)

Parameter	Min	Typ	Max	Unit
Gate bias voltage		-2.3		V
Drain working voltage		28(pulse)/26(CW)		V
Quiescent drain current		2(pulse)/1.8(CW)		A
Dynamic drain current		3.1(pulse)/2.8(CW)		A

Microwave electrical parameters (T_A=+25°C, V_d=+28V, V_g=-2.3V, 10%Duty cycle, cycle 1ms)

Parameter	Min	Typ	Max	Unit
Frequency range	6.0~18.0			GHz
Psat	41.8	43	44.2	dBm
PAE		25		%
Power gain (@Pin=22dBm)		18.5		dB
Power gain flatness		±1.5		dB
Input/output return loss		-13/-6		dB

Absolute maximum ratings ^[1]

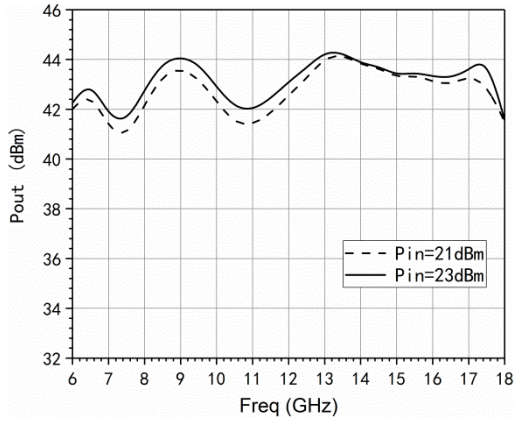
Parameter	Ratings
Drain voltage	+30V
Input power	30dBm
Operating temperature	-55°C~+85°C
Storage temperature	-65°C~+120°C

[1] Exceeding any of these limits may cause permanent damage.

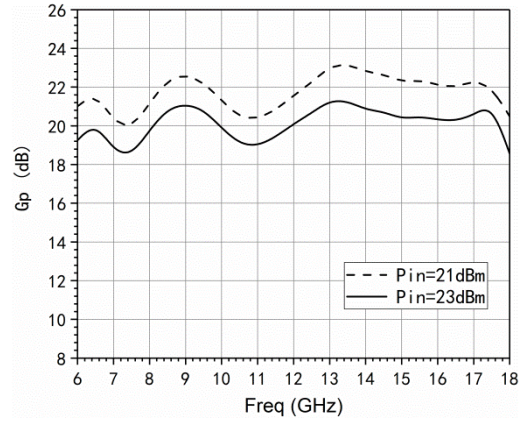
GaN MMIC Power Amplifier Chip, 6.0-18.0 GHz

Typical performance curves ($T_A=+25^\circ\text{C}$, $V_d=+28\text{V}$, $V_g=-2.3\text{V}$, 10% Duty cycle, cycle 1ms)

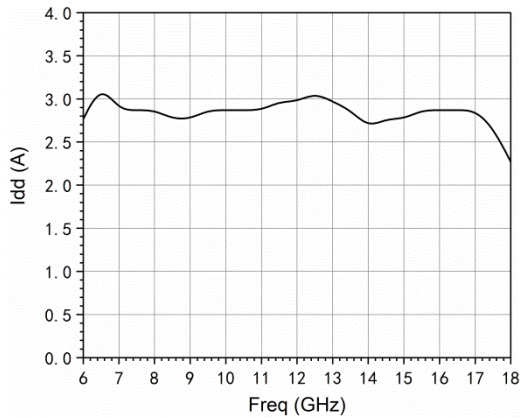
Output power vs. frequency



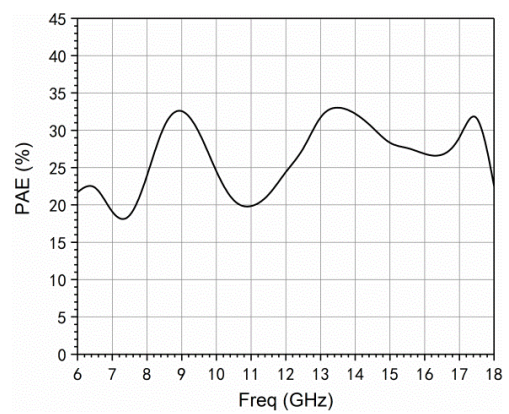
Power gain vs. frequency



Dynamic current vs. frequency(@Pin=23dBm)

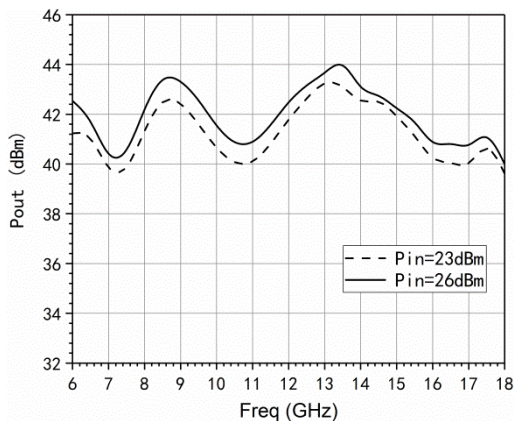


Power added efficiency vs. frequency(@Pin=23dBm)

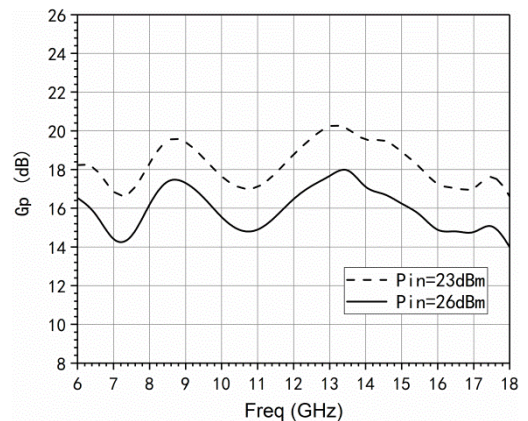


Typical performance curves ($T_A=+25^\circ\text{C}$, $V_d=+26\text{V}$, $V_g=-2.3\text{V}$, CW)

Output power vs. frequency

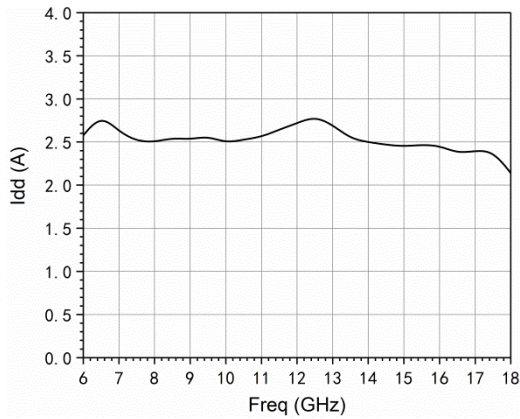


Power gain vs. frequency

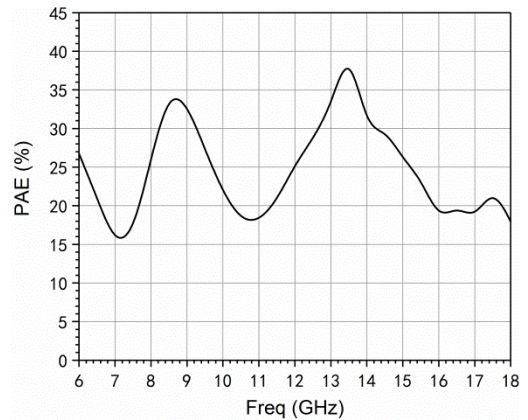


GaN MMIC Power Amplifier Chip, 6.0-18.0 GHz

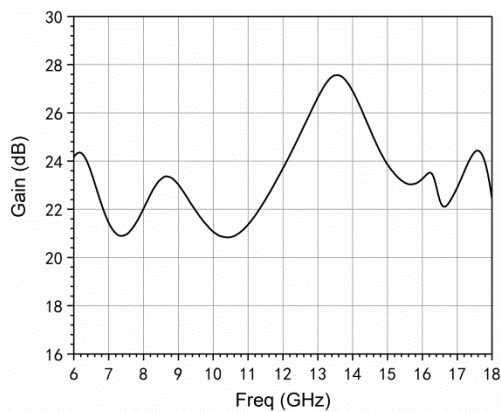
Dynamic current vs. frequency (@Pin=26dBm)



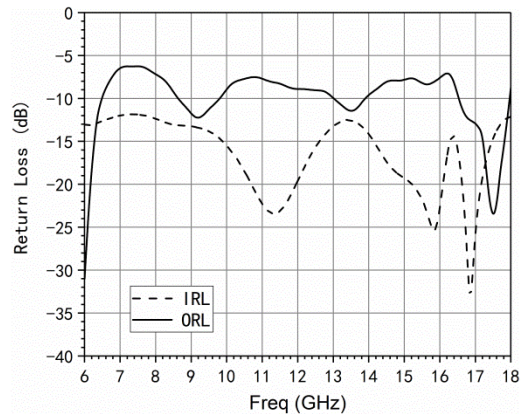
Power added efficiency vs. frequency (@Pin=26dBm)



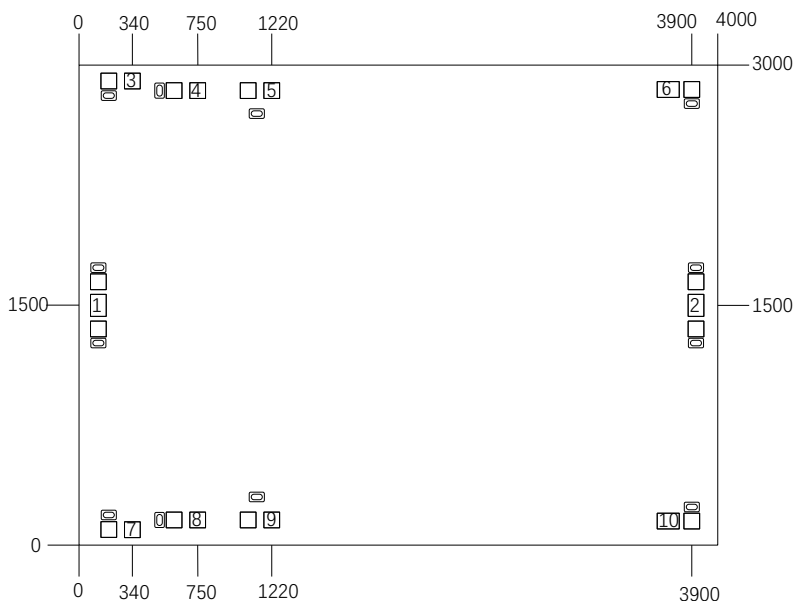
Small signal gain vs. frequency (@Pin=-10dBm)



Input/output return loss vs. frequency



Outline Dimensions



Notes:

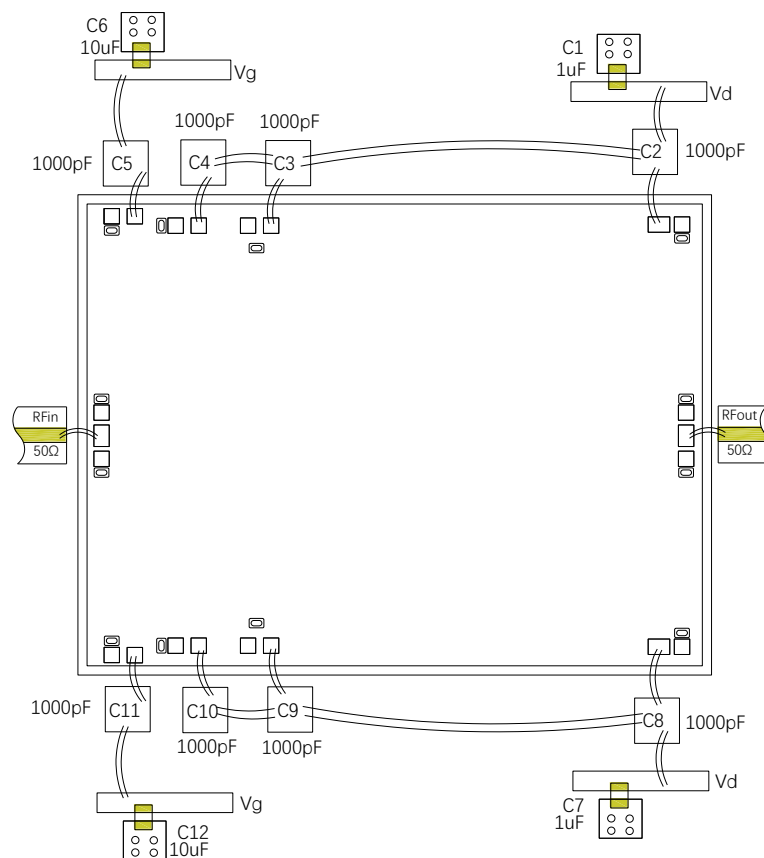
1. Unit: μm
2. Gold plating on bonding pads
3. Dimensional tolerance: $\pm 20 \mu\text{m}$

GaN MMIC Power Amplifier Chip, 6.0-18.0 GHz

Pad Definition

Pad Number	Function	Description	Dimensions
1	IN	RF input terminal, external 50 ohm system, no need for external blocking capacitor	100×120um
2	OUT	RF output terminal, external 50 ohm system, no need for external blocking capacitor	100×120um
4、5、8、9	Vd	Drain power supply	100×100um
6、10	Vd	Drain power supply	140×100um
3、7	Vg	Gate power supply	100×100um

Suggested assembly diagram



Note: To ensure more stable performance of the amplifier, it is recommended to weld ceramic capacitors with the recommended capacitance values in the above assembly diagram at the feeding end for filtering. The number of filtering capacitors can also be increased or different capacitance values can be combined according to actual needs.

Note:

1. Please assemble and use in a purified environment, store in anti-static containers, and keep dry
2. The back of the chip is grounded with gold backing. Please ensure that the back is in full contact with the ground and well grounded during use
3. Use gold tin solder with a ratio of 80/20 to sinter, with a sintering temperature not exceeding 300 °C and a sintering time as short as possible, not exceeding 20 seconds
4. This product is an electrostatic sensitive device. Please pay attention to anti-static measures during storage and use
5. Do not attempt to clean the surface of the chip using dry or wet chemical methods
6. If you have any questions, please contact the supplier



This product is sensitive to static electricity. Please pay attention to anti-static measures during use